MARKING



Inverting Regulator - Buck, Boost, Switching

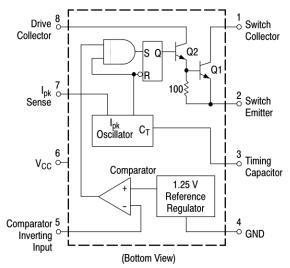
1.5 A

MC34063A, MC33063A, SC34063A, SC33063A, NCV33063A

The MC34063A Series is a monolithic control circuit containing the primary functions required for DC-to-DC converters. These devices consist of an internal temperature compensated reference, comparator, controlled duty cycle oscillator with an active current limit circuit, driver and high current output switch. This series was specifically designed to be incorporated in Step-Down and Step-Up and Voltage-Inverting applications with a minimum number of external components. Refer to Application Notes AN920A/D and AN954/D for additional design information.

Features

- Operation from 3.0 V to 40 V Input
- Low Standby Current
- Current Limiting
- Output Switch Current to 1.5 A
- Output Voltage Adjustable
- Frequency Operation to 100 kHz
- Precision 2% Reference
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

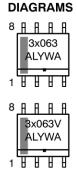


This device contains 79 active transistors.

Figure 1. Representative Schematic Diagram

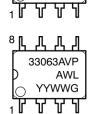


SOIC-8 D SUFFIX CASE 751





PDIP-8 P, P1 SUFFIX CASE 626



3x063AP1

YYWWG

AWL



DFN8 CASE 488AF



x = 3 or 4

A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

Figure 2. Pin Connections

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|-------------------------|-------------|------|
| Power Supply Voltage | V _{CC} | 40 | Vdc |
| Comparator Input Voltage Range | V _{IR} | -0.3 to +40 | Vdc |
| Switch Collector Voltage | V _{C(switch)} | 40 | Vdc |
| Switch Emitter Voltage (V _{Pin 1} = 40 V) | V _{E(switch)} | 40 | Vdc |
| Switch Collector to Emitter Voltage | V _{CE(switch)} | 40 | Vdc |
| Driver Collector Voltage | V _{C(driver)} | 40 | Vdc |
| Driver Collector Current (Note 1) | I _{C(driver)} | 100 | mA |
| Switch Current | I _{SW} | 1.5 | А |
| Power Dissipation and Thermal Characteristics | | | |
| Plastic Package, P, P1 Suffix | | | |
| T _A = 25°C | P _D | 1.25 | W |
| Thermal Resistance | $R_{	heta JA}$ | 115 | °C/W |
| SOIC Package, D Suffix | | | |
| T _A = 25°C | P _D | 625 | mW |
| Thermal Resistance | $R_{	heta JA}$ | 160 | °C/W |
| Thermal Resistance | $R_{	heta JC}$ | 45 | °C/W |
| DFN Package | | | |
| T _A = 25°C | P _D | 1.25 | mW |
| Thermal Resistance | $R_{	heta JA}$ | 80 | °C/W |
| Operating Junction Temperature | TJ | +150 | °C |
| Operating Ambient Temperature Range | T _A | | °C |
| MC34063A, SC34063A | | 0 to +70 | |
| MC33063AV, NCV33063A | | -40 to +125 | |
| MC33063A, SC33063A | | -40 to +85 | |
| Storage Temperature Range | T _{stg} | -65 to +150 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

^{1.} Maximum package power dissipation limits must be observed.

This device series contains ESD protection and exceeds the following tests: Human Body Model 4000 V per MIL-STD-883, Method 3015.
 Machine Model Method 400 V.

^{3.} NCV prefix is for automotive and other applications requiring site and change control.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0 \text{ V}$, $T_A = T_{low}$ to T_{high} [Note 4], unless otherwise specified.)

| Characteristics | Symbol | Min | Тур | Max | Unit |
|--|---------------------------------------|---------------|------------|---------------|------|
| OSCILLATOR | • | • | | | |
| Frequency ($V_{Pin 5} = 0 \text{ V, } C_T = 1.0 \text{ nF, } T_A = 25^{\circ}\text{C}$) | f _{osc} | 24 | 33 | 42 | kHz |
| Charge Current (V _{CC} = 5.0 V to 40 V, T _A = 25°C) | I _{chg} | 24 | 35 | 42 | μΑ |
| Discharge Current (V _{CC} = 5.0 V to 40 V, T _A = 25°C) | I _{dischg} | 140 | 220 | 260 | μΑ |
| Discharge to Charge Current Ratio (Pin 7 to V _{CC} , T _A = 25°C) | I _{dischg} /I _{chg} | 5.2 | 6.5 | 7.5 | - |
| Current Limit Sense Voltage (I _{chg} = I _{dischg} , T _A = 25°C) | V _{ipk(sense)} | 250 | 300 | 350 | mV |
| OUTPUT SWITCH (Note 5) | | | | | |
| Saturation Voltage, Darlington Connection (I _{SW} = 1.0 A, Pins 1, 8 connected) | V _{CE(sat)} | - | 1.0 | 1.3 | V |
| Saturation Voltage (Note 6) (I _{SW} = 1.0 A, R _{Pin 8} = 82 Ω to V _{CC} , Forced $\beta \simeq$ 20) | V _{CE(sat)} | - | 0.45 | 0.7 | V |
| DC Current Gain (I _{SW} = 1.0 A, V _{CE} = 5.0 V, T _A = 25°C) | h _{FE} | 50 | 75 | - | - |
| Collector Off-State Current (V _{CE} = 40 V) | I _{C(off)} | - | 0.01 | 100 | μΑ |
| COMPARATOR | • | | | | |
| Threshold Voltage $T_A = 25^{\circ}C$ $T_A = T_{low}$ to T_{high} | V _{th} | 1.225 1.21 | 1.25 - | 1.275 1.29 | V |
| Threshold Voltage Line Regulation (V _{CC} = 3.0 V to 40 V) MC33063, MC34063 MC33063V, NCV33063 | Reg _{line} | - - | 1.4 1.4 | 5.0 6.0 | mV |
| Input Bias Current (V _{in} = 0 V) | I _{IB} | - | -20 | -400 | nA |
| TOTAL DEVICE | | | | | |
| Supply Current (V_{CC} = 5.0 V to 40 V, C_T = 1.0 nF, Pin 7 = V_{CC} , $V_{Pin 5}$ > V_{th} , Pin 2 = GND, remaining pins open) | Icc | - | - | 4.0 | mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Forced β of output switch : $\frac{IC \text{ output}}{IC \text{ driver} - 7.0 \text{ mA}^*} \ge 10$

^{4.} T_{low} = 0°C for MC34063, SC34063; −40°C for MC33063, SC33063, MC33063V, NCV33063

T_{high} = +70°C for MC34063, SC34063; +85°C for MC33063, SC33063; +125°C for MC33063V, NCV33063

5. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.

6. If the output switch is driven into hard saturation (non-Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 µs for it to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non-Darlington configuration is used, the following output drive condition is recommended:

^{*}The 100 Ω resistor in the emitter of the driver device requires about 7.0 mA before the output switch conducts.

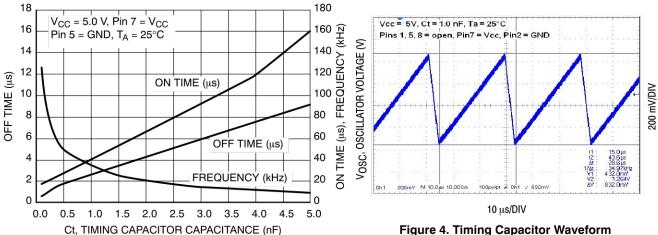


Figure 3. Oscillator Frequency

Figure 4. Timing Capacitor Waveform

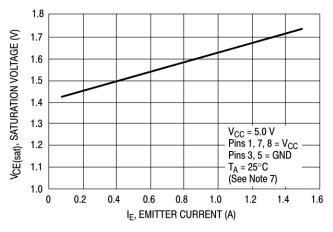


Figure 5. Emitter Follower Configuration Output Saturation Voltage versus Emitter Current

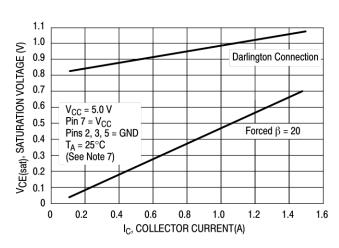


Figure 6. Common Emitter Configuration Output Switch Saturation Voltage versus **Collector Current**

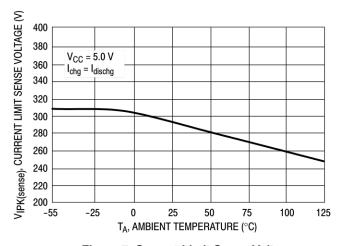


Figure 7. Current Limit Sense Voltage versus Temperature

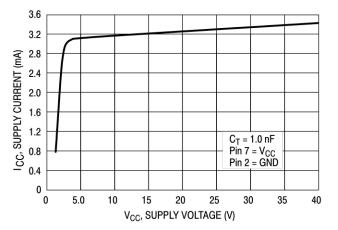
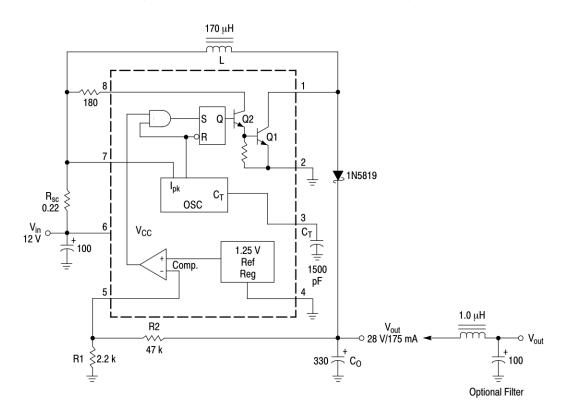


Figure 8. Standby Supply Current versus Supply Voltage

7. Low duty cycle pulse techniques are used during test to maintain junction temperature as close to ambient temperature as possible.



| Test | Conditions | Results |
|------------------------------------|--|-----------------|
| Line Regulation | V _{in} = 8.0 V to 16 V, I _O = 175 mA | 30 mV = ±0.05% |
| Load Regulation | V _{in} = 12 V, I _O = 75 mA to 175 mA | 10 mV = ±0.017% |
| Output Ripple | V _{in} = 12 V, I _O = 175 mA | 400 mVpp |
| Efficiency | V _{in} = 12 V, I _O = 175 mA | 87.7% |
| Output Ripple With Optional Filter | V _{in} = 12 V, I _O = 175 mA | 40 mVpp |

Figure 9. Step-Up Converter

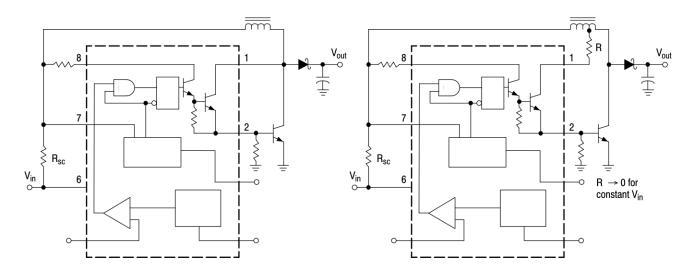


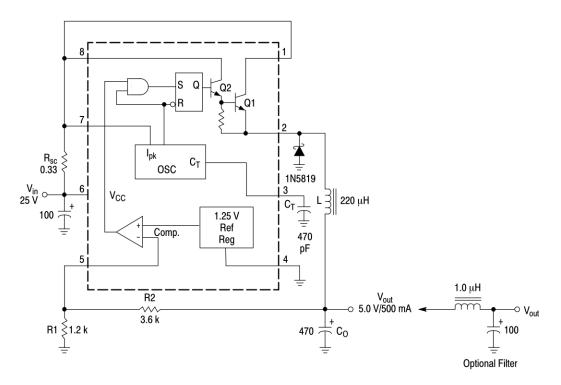
Figure 10. External Current Boost Connections for I_C Peak Greater than 1.5 A

9a. External NPN Switch

9b. External NPN Saturated Switch

(See Note 8)

8. If the output switch is driven into hard saturation (non–Darlington configuration) at low switch currents (≤ 300 mA) and high driver currents (≥ 30 mA), it may take up to 2.0 μs to come out of saturation. This condition will shorten the off time at frequencies ≥ 30 kHz, and is magnified at high temperatures. This condition does not occur with a Darlington configuration, since the output switch cannot saturate. If a non–Darlington configuration is used, the following output drive condition is recommended.



| Test | Conditions | Results |
|------------------------------------|--|-----------------|
| Line Regulation | V _{in} = 15 V to 25 V, I _O = 500 mA | 12 mV = ±0.12% |
| Load Regulation | V _{in} = 25 V, I _O = 50 mA to 500 mA | 3.0 mV = ±0.03% |
| Output Ripple | V _{in} = 25 V, I _O = 500 mA | 120 mVpp |
| Short Circuit Current | V_{in} = 25 V, R_L = 0.1 Ω | 1.1 A |
| Efficiency | V _{in} = 25 V, I _O = 500 mA | 83.7% |
| Output Ripple With Optional Filter | V _{in} = 25 V, I _O = 500 mA | 40 mVpp |

Figure 11. Step-Down Converter

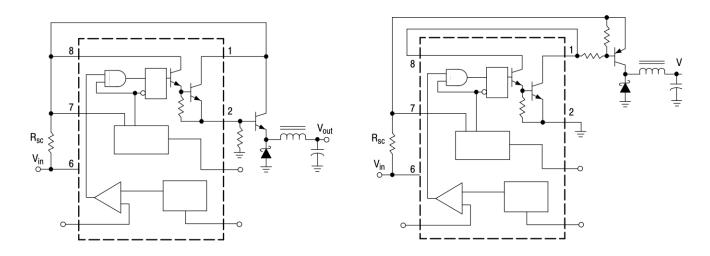
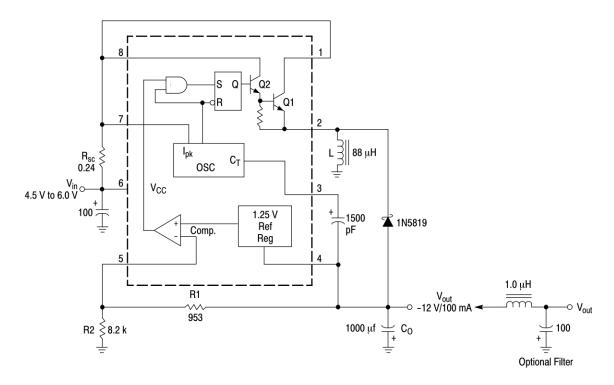


Figure 12. External Current Boost Connections for $I_{\mathbb{C}}$ Peak Greater than 1.5 A

11a. External NPN Switch

11b. External PNP Saturated Switch



| Test | Conditions | Results |
|------------------------------------|---|------------------|
| Line Regulation | V _{in} = 4.5 V to 6.0 V, I _O = 100 mA | 3.0 mV = ±0.012% |
| Load Regulation | V _{in} = 5.0 V, I _O = 10 mA to 100 mA | 0.022 V = ±0.09% |
| Output Ripple | V _{in} = 5.0 V, I _O = 100 mA | 500 mVpp |
| Short Circuit Current | $V_{in} = 5.0 \text{ V}, R_L = 0.1 \Omega$ | 910 mA |
| Efficiency | V _{in} = 5.0 V, I _O = 100 mA | 62.2% |
| Output Ripple With Optional Filter | V _{in} = 5.0 V, I _O = 100 mA | 70 mVpp |

Figure 13. Voltage Inverting Converter

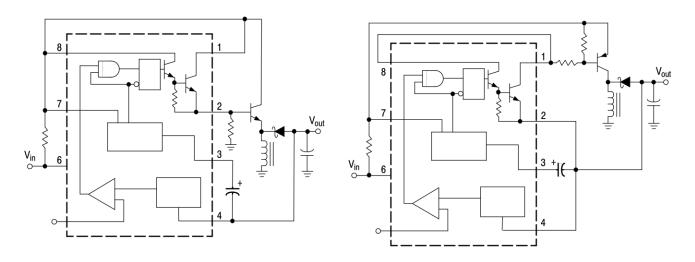
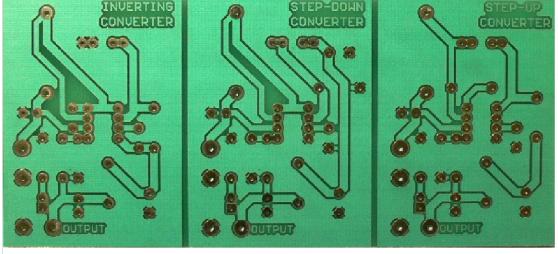


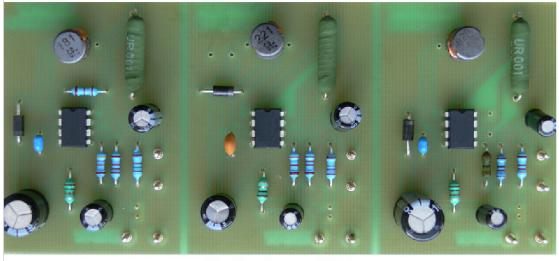
Figure 14. External Current Boost Connections for I_C Peak Greater than 1.5 A

13a. External NPN Switch

13b. External PNP Saturated Switch



(Bottom Side)



(Top View, Component Side)

Figure 15. Printed Circuit Board and Component Layout

(Circuits of Figures 9, 11, 13)

INDUCTOR DATA

| Converter Inductance (μH) | | Turns/Wire |
|---------------------------|-----|---------------------|
| Step-Up | 170 | 38 Turns of #22 AWG |
| Step-Down | 220 | 48 Turns of #22 AWG |
| Voltage-Inverting | 88 | 28 Turns of #22 AWG |

All inductors are wound on Magnetics Inc. 55117 toroidal core.

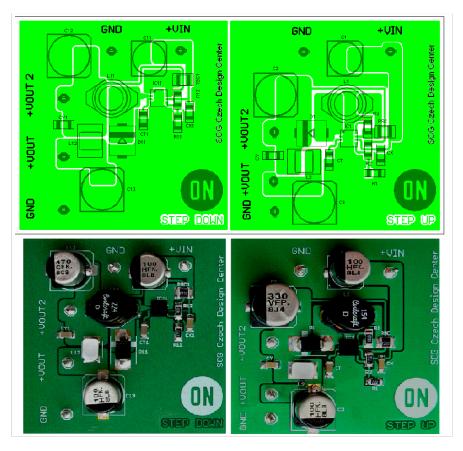


Figure 16. Printed Circuit Board for DFN Device

| Calculation | Step-Up | Step-Down | Voltage-Inverting |
|---------------------------------------|---|--|---|
| t _{on} /t _{off} | $\frac{V_{out} + V_{F} - V_{in(min)}}{V_{in(min)} - V_{sat}}$ | $\frac{V_{out} + V_{F}}{V_{in(min)} - V_{sat} - V_{out}}$ | $\frac{ V_out \ + \ V_F}{V_in \ - \ V_sat}$ |
| (t _{on} + t _{off}) | <u>1</u> | <u>1</u> f | $\frac{1}{f}$ |
| t _{off} | $\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}}} + 1$ | $\frac{\frac{t_{on} + t_{off}}{t_{on}}}{\frac{t_{on}}{t_{off}} + 1}$ | $\frac{t_{\text{on}} + t_{\text{off}}}{\frac{t_{\text{on}}}{t_{\text{off}}}} + 1$ |
| t _{on} | $(t_{on} + t_{off}) - t_{off}$ | $(t_{on} + t_{off}) - t_{off}$ | $(t_{on} + t_{off}) - t_{off}$ |
| C _T | $4.0 \times 10^{-5} t_{on}$ | $4.0 \times 10^{-5} t_{on}$ | $4.0 \times 10^{-5} t_{on}$ |
| I _{pk(switch)} | $2I_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1\right)$ | ^{2I} out(max) | $2I_{out(max)} \left(\frac{t_{on}}{t_{off}} + 1\right)$ |
| R _{sc} | 0.3/I _{pk(switch)} | 0.3/I _{pk(switch)} | 0.3/I _{pk(switch)} |
| L _(min) | $\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}})}{I_{\text{pk(switch)}}}\right)^{t} \text{on(max)}$ | $\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}} - V_{\text{out}})}{I_{\text{pk(switch)}}}\right) t_{\text{on(max)}}$ | $\left(\frac{(V_{\text{in(min)}} - V_{\text{sat}})}{I_{\text{pk(switch)}}}\right)^{t_{\text{on(max)}}}$ |
| Co | 9 | $\frac{I_{pk(switch)}^{(t_{on} + t_{off})}}{8V_{ripple(pp)}}$ | $9 \frac{I_{out}^{t_{on}}}{V_{ripple(pp)}}$ |

V_{sat} = Saturation voltage of the output switch.

The following power supply characteristics must be chosen:

V_{in} - Nominal input voltage.

 V_{out} - Desired output voltage, $|V_{out}| = 1.25 \left(1 + \frac{R2}{R1}\right)$

I_{out} – Desired output current.

 f_{min} – Minimum desired output switching frequency at the selected values of V_{in} and I_{O} .

V_{ripple(pp)} – Desired peak-to-peak output ripple voltage. In practice, the calculated capacitor value will need to be increased due to its equivalent series resistance and board layout. The ripple voltage should be kept to a low value since it will directly affect the line and load regulation.

NOTE: For further information refer to Application Note AN920A/D and AN954/D.

Figure 17. Design Formula Table

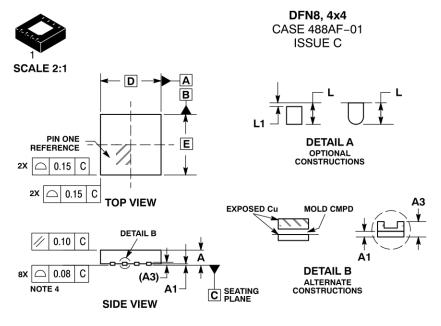
V_F = Forward voltage drop of the output rectifier.

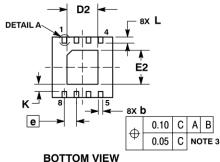
ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------------|---------------------|--------------------------|
| MC33063ADG | SOIC-8 (Pb-Free) | 98 Units / Rail |
| MC33063ADR2G | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| SC33063ADR2G | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| MC33063AP1G | PDIP-8 (Pb-Free) | 50 Units / Rail |
| MC33063AVDG | SOIC-8 (Pb-Free) | 98 Units / Rail |
| MC33063AVDR2G | SOIC-8 (Pb-Free) | |
| NCV33063AVDR2G* | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| MC33063AVPG | PDIP-8 (Pb-Free) | 50 Units / Rail |
| MC34063ADG | SOIC-8 (Pb-Free) | 98 Units / Rail |
| MC34063ADR2G | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| SC34063ADR2G | SOIC-8 (Pb-Free) | 2500 Units / Tape & Reel |
| MC34063AP1G | PDIP-8 (Pb-Free) | 50 Units / Rail |
| SC34063AP1G | PDIP-8 (Pb-Free) | 50 Units / Rail |
| MC33063MNTXG | DFN8 (Pb-Free) | 4000 Units / Tape & Reel |

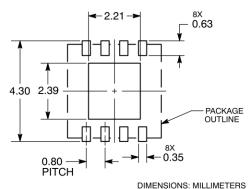
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

^{*}NCV33063A: T_{low} = -40°C, T_{high} = +125°C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.





SOLDERING FOOTPRINT*



DATE 15 JAN 2009

NOTES:

- 1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION 6 APPLIES TO PLATED
 TERMINAL AND IS MEASURED BETWEEN
 0.15 AND 0.30MM FROM TERMINAL TIP.
 COPLANARITY APPLIES TO THE EXPOSED
- PAD AS WELL AS THE TERMINALS.
 5. DETAILS A AND B SHOW OPTIONAL CON-STRUCTIONS FOR TERMINALS.

| | MILLIMETERS | | |
|-----|-------------|------|--|
| DIM | MIN | MAX | |
| Α | 0.80 | 1.00 | |
| A1 | 0.00 | 0.05 | |
| А3 | 0.20 | REF | |
| b | 0.25 | 0.35 | |
| D | 4.00 | BSC | |
| D2 | 1.91 | 2.21 | |
| Е | 4.00 | BSC | |
| E2 | 2.09 | 2.39 | |
| е | 0.80 BSC | | |
| K | 0.20 | | |
| Г | 0.30 | 0.50 | |
| L1 | | 0.15 | |

GENERIC MARKING DIAGRAM*



XXXX = Specific Device Code

Α = Assembly Location = Wafer Lot L Υ = Year

W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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|------------------|-----------------|--|-------------|
| DESCRIPTION: | DFN8, 4X4, 0.8P | | PAGE 1 OF 1 |

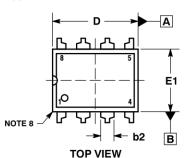
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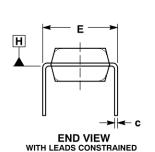
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

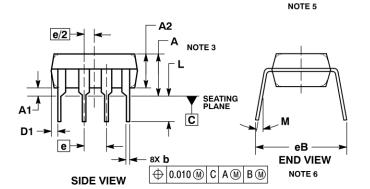


PDIP-8 CASE 626-05 **ISSUE P**

DATE 22 APR 2015







STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN 5. GROUND 6. OUTPUT 7. AUXILIARY 8. V_{CC}

NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
 DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH
 OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
 NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- DIMENSION &B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.

 DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

| | INCHES | | MILLIM | ETERS |
|-----|-----------|-------|--------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | | 0.210 | | 5.33 |
| A1 | 0.015 | | 0.38 | |
| A2 | 0.115 | 0.195 | 2.92 | 4.95 |
| b | 0.014 | 0.022 | 0.35 | 0.56 |
| b2 | 0.060 | TYP | 1.52 | TYP |
| С | 0.008 | 0.014 | 0.20 | 0.36 |
| D | 0.355 | 0.400 | 9.02 | 10.16 |
| D1 | 0.005 | | 0.13 | |
| Е | 0.300 | 0.325 | 7.62 | 8.26 |
| E1 | 0.240 | 0.280 | 6.10 | 7.11 |
| е | 0.100 BSC | | 2.54 | BSC |
| eВ | | 0.430 | | 10.92 |
| L | 0.115 | 0.150 | 2.92 | 3.81 |
| М | | 10° | | 10° |

GENERIC MARKING DIAGRAM*



= Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

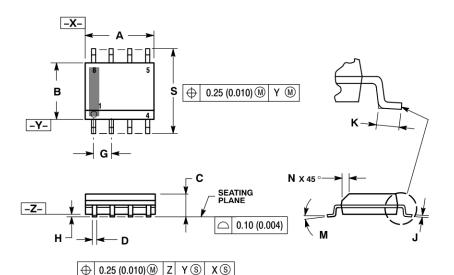
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SOIC-8 NB CASE 751-07 **ISSUE AK**

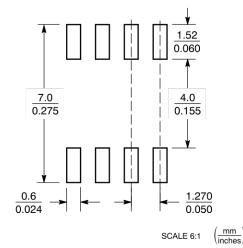
DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

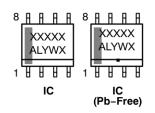
| | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| DIM | MIN | MAX | MIN | MAX |
| Α | 4.80 | 5.00 | 0.189 | 0.197 |
| В | 3.80 | 4.00 | 0.150 | 0.157 |
| O | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| Н | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| М | 0 ° | 8 ° | 0 ° | 8 ° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| s | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



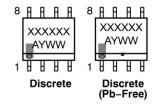
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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| STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER STYLE 5: PIN 1. DRAIN | STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6: PIN 1. SOURCE | STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS | STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE STYLE 8: PIN 1. COLLECTOR, DIE #1 |
|--|---|---|---|
| 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE | 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE | THIRD STAGE SOURCE GROUND DRAIN GATE 3 SECOND STAGE Vd FIRST STAGE Vd | 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1 |
| STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON | STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND | STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1 | STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN |
| STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN | STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN | STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON | STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1 |
| STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC | STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE | STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1 | STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN |
| STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6 | STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND | STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT | STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE |
| STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT | STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC | STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN | STYLE 28: PIN 1. SW TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN |
| STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1 | STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1 | | |

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